





SN74AXC4T245

SCES877A - DECEMBER 2018 - REVISED JULY 2020

SN74AXC4T245 Four-Bit Bus Transceiver with Configurable Voltage Translation and Tri-State Outputs

1 Features

Texas

INSTRUMENTS

- Fully Configurable Dual-Rail Design Allows Each Port to Operate With a Power Supply Range From 0.65 V to 3.6 V
- Operating Temperature From -40°C to +125°C
- Multiple Direction Control Pins to Allow Simultaneous Up and Down Translation
- Glitch-Free Power Supply Sequencing
- Up to 380 Mbps Support When Translating from 1.8 V to 3.3 V
- V_{CC} Isolation Feature
 - If Either V_{CC} Input is Below 100 mV, All I/Os Outputs are Disabled and Become High-Impedance
- Ioff Supports Partial-Power-Down Mode Operation
- Compatible With AVC Family Level Shifters
- Latch-Up Performance Exceeds 100 mA Per JESD 78. Class II
- ESD Protection Exceeds JESD 22
 - 8000-V Human-Body Model
 - 1000-V Charged-Device Model _

2 Applications

- **Enterprise and Communications**
- Industrial
- **Personal Electronics**
- Wireless Infrastructure
- **Building Automation**
- Point of Sale •

3 Description

The SN74AXC4T245 is a four-bit noninverting bus transceiver that uses two individually configurable power-supply rails. The device is operational with both V_{CCA} and V_{CCB} supplies as low as 0.65 V. The A port is designed to track $V_{\text{CCA}},$ which accepts any supply voltage from 0.65 V to 3.6 V. The B port is designed to track V_{CCB}, which also accepts any supply voltage from 0.65 V to 3.6 V. Additionally the SN74AXC4T245 is compatible with a single-supply system.

The SN74AXC4T245 is device designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level of the direction-control inputs (1DIR and 2DIR). The output-enable inputs (1 \overline{OE} and 2 \overline{OE}) are used to disable the outputs so the buses are effectively isolated. The SN74AXC4T245 device is designed so the control pins (xDIR and x \overline{OE}) are referenced to V_{CCA}.

To ensure the high-impedance state of the level shifter I/Os during power up or power down, the x $\overline{\text{OE}}$ pins should be tied to V_{CCA} through a pullup resistor.

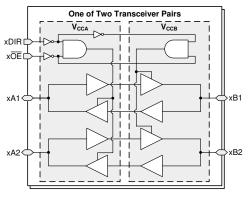
This device is fully specified for partial-power-down applications using the Ioff current. The Ioff protection circuitry ensures that no excessive current is drawn from or to an input, output, or combined I/O that is biased to a specific voltage while the device is powered down.

The V_{CC} isolation feature ensures that if either V_{CCA} or V_{CCB} is less than 100 mV, both I/O ports enter a high-impedance state by disabling their outputs.

Glitch-Free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

De	Device Information													
PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)												
SN74AXC4T245PW	TSSOP (16)	5.00 mm x 4.40 mm												
SN74AXC4T245BQB	WQFN (16)	2.50 mm x 3.50 mm												
SN74AXC4T245RSV	UQFN (16)	2.60 mm x 1.80 mm												

For all available packages, see the orderable addendum at (1) the end of the data sheet.



Functional Block Diagram





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4 Revision History

Cł	hanges from Revision * (December 2018) to Revision A (July 2020)	Page
•	Updated the numbering format for tables, figures and cross-references throughout the document	1



5 Pin Configuration and Functions

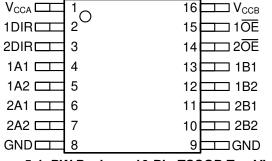


Figure 5-1. PW Package 16-Pin TSSOP Top View

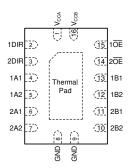


Figure 5-2. BQB Package 16-Pin WQFN Transparent Top View

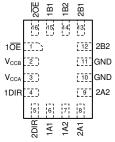


Figure 5-3. RSV Package 16-Pin UQFN Transparent Top View

PIN NO.					DESCRIPTION
NAME	PW	RSV	BQB	TYPE	DESCRIPTION
1A1	4	6	4	I/O	Input/output 1A1. Referenced to V _{CCA} .
1A2	5	7	5	I/O	Input/output 1A2. Referenced to V _{CCA} .
1B1	13	15	13	I/O	Input/output 1B1. Referenced to V _{CCB} .
1B2	12	14	12	I/O	Input/output 1B2. Referenced to V _{CCB} .
1DIR	2	4	2	I	Direction-control input for '1' ports.
1 OE	15	1	15	I	Tri-state output-mode enable. Pull $\overline{\text{OE}}$ high to place '1' outputs in tri-state mode. Referenced to V_{CCA} .
2A1	6	8	6	I/O	Input/output 2A1. Referenced to V _{CCA} .
2A2	7	9	7	I/O	Input/output 2A2. Referenced to V _{CCA} .
2B1	11	13	11	I/O	Input/output 2B1. Referenced to V _{CCB} .
2B2	10	12	10	I/O	Input/output 2B2. Referenced to V _{CCB} .
2DIR	3	5	3	I	Direction-control input for '2' ports.
2 <u>OE</u>	14	16	14	I	Tri-state output-mode enable. Pull $\overline{\text{OE}}$ high to place '2' outputs in tri-state mode. Referenced to V_{CCA} .
GND	8, 9	10, 11	8, 9	_	Ground.
V _{CCA}	1	3	1	_	A-port power supply voltage. 0.65 V \leq V _{CCA} \leq 3.6 V.
V _{CCB}	16	2	16	_	B-port power supply voltage. $0.65 \text{ V} \le \text{V}_{\text{CCB}} \le 3.6 \text{ V}.$

Table 5-1. Pin Functions



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CCA}	Supply voltage A		-0.5	4.2	V
V _{CCB}	Supply voltage B		-0.5	4.2	V
		I/O Ports (A Port)	-0.5	4.2	
VI	Input Voltage ⁽²⁾	I/O Ports (B Port)	-0.5	4.2	V
		Control Inputs	-0.5	4.2	
V	Valtage applied to any output in the high impedance or neuror off state $\binom{2}{2}$	A Port	-0.5	4.2	V
Vo	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	B Port	-0.5	4.2	v
v	Voltage explicit to any extruct in the high or law state(2) (3)	A Port	-0.5	V _{CCA} + 0.2	V
Vo	Voltage applied to any output in the high or low state ^{(2) (3)}	B Port	-0.5	V _{CCB} + 0.2	v
I _{IK}	Input clamp current	V _I < 0	-50		mA
I _{OK}	Output clamp current	V _O < 0	-50		mA
I _O	Continuous output current		-50	50	mA
	Continuous current through V _{CC} or GND		-100	100	mA
Tj	Junction Temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.2 V maximum if the output current rating is observed.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±8000	V
V _(ESD)		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

			· · · ·	MIN	MAX	UNIT
V _{CCA}	Supply voltage A			0.65	3.6	V
V _{CCB}	Supply voltage B			0.65	3.6	V
			V _{CCI} = 0.65 V - 0.75 V	V _{CCI} x 0.70		
			V _{CCI} = 0.76 V - 1 V	V _{CCI} x 0.70		
		Data Inputs	V _{CCI} = 1.1 V - 1.95 V	V _{CCI} x 0.65		
VIH			V _{CCI} = 2.3 V - 2.7 V	1.6		
	Lligh lovel input veltage		V _{CCI} = 3 V - 3.6 V	2		V
	High-level input voltage		V _{CCA} = 0.65 V - 0.75 V	V _{CCA} x 0.70		v
			V _{CCA} = 0.76 V - 1 V	V _{CCA} x 0.70		
		Control Inputs(xDIR, x \overline{OE}) Referenced to V _{CCA}	V _{CCA} = 1.1 V - 1.95 V	V _{CCA} x 0.65		
			V _{CCA} = 2.3 V - 2.7 V	1.6		
			V _{CCA} = 3 V - 3.6 V	2		
			V _{CCI} = 0.65 V - 0.75 V		V _{CCI} x 0.30	
			V _{CCI} = 0.76 V - 1 V		V _{CCI} x 0.30	
		Data Inputs	V _{CCI} = 1.1 V - 1.95 V		V _{CCI} x 0.35	
			V _{CCI} = 2.3 V - 2.7 V		0.7	
,			V _{CCI} = 3 V - 3.6 V		0.8	V
/ _{IL}	Low-level input voltage		V _{CCA} = 0.65 V - 0.75 V		V _{CCA} x 0.30	V
			V _{CCA} = 0.76 V - 1 V		V _{CCA} x 0.30	
		Control Inputs(xDIR, x \overline{OE}) Referenced to V _{CCA}	V _{CCA} = 1.1 V - 1.95 V		V _{CCA} x 0.35	
			V _{CCA} = 2.3 V - 2.7 V		0.7	
			V _{CCA} = 3 V - 3.6 V		0.8	
' 1	Input voltage ⁽²⁾			0	3.6	V
′o	Output voltage	Active State		0	V _{cco}	V
-		Tri-State	0 3.6			
t/∆v <mark>(2)</mark>	Input transition rate				10	ns/V
A	Operating free-air tempe	rature		-40	125	°C

(1)

 V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. All unused inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, (2) Implications of Slow or Floating CMOS Inputs.

6.4 Thermal Information

		SN74AXC4T245								
	THERMAL METRIC ⁽¹⁾	PW (TSSOP)	RSV (UQFN)	BQB (WQFN)	UNIT					
		16 PINS	16 PINS	16 PINS						
R _{θJA}	Junction-to-ambient thermal resistance	126.9	130.1	73.0	°C/W					
R _{0JC(top)}	Junction-to-case (top) thermal resistance	49.3	70.3	35.1	°C/W					
R _{0JB}	Junction-to-board thermal resistance	74.3	57.4	42.8	°C/W					
Ψ _{JT}	Junction-to-top characterization parameter	8.1	4.6	4.6	°C/W					
Ψ _{JB}	Junction-to-board characterization parameter	73.4	55.8	42.8	°C/W					
R _{0JC(bottom)}	Junction-to-case (bottom) thermal resistance	NA	NA	10.2	°C/W					

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application (1) report.



6.5 Electrical Characteristics

						0	Operating free-a	r tempera	ture (T _A)			
PARAMETER		TEST	CONDITIONS	V _{CCA}	V _{CCB}	-40)°C to 85°C	-40	UNIT			
						MIN	TYP ⁽⁴⁾ MAX	MIN	TYP ⁽⁴⁾	MAX		
			I _{OH} = -100 μA	0.7 V - 3.6 V	0.7 V - 3.6 V	V _{CCO} – 0.1		V _{CCO} – 0.1				
			I _{OH} = –50 μA	0.65 V	0.65 V	0.55		0.55				
			I _{OH} = -200 μA	0.76 V	0.76 V	0.58		0.58				
	High-level output		I _{OH} = –500 μA	0.85 V	0.85 V	0.65		0.65				
/ _{он}	voltage	$V_{I} = V_{IH}$	I _{OH} = -3 mA	1.1 V	1.1 V	0.85		0.85			V	
			I _{OH} = -6 mA	1.4 V	1.4 V	1.05		1.05				
			I _{OH} =8 mA	1.65 V	1.65 V	1.2		1.2				
			I _{OH} = –9 mA	2.3 V	2.3 V	1.75		1.75				
			I _{OH} = -12 mA	3 V	3 V	2.3		2.3				
			I _{OL} = 100 μA	0.7 V - 3.6 V	0.7 V - 3.6 V		0.1			0.1		
			I _{OL} = 50 μA	0.65 V	0.65 V		0.1			0.1		
			I _{OL} = 200 μA	0.76 V	0.76 V		0.18	,		0.18		
			I _{OL} = 500 μA	0.85 V	0.85 V		0.2	:		0.2		
/ _{OL}	Low-level output voltage	V _I = V _{IL}	I _{OL} = 3 mA	1.1 V	1.1 V		0.25			0.25	V	
	voltage		I _{OL} = 6 mA	1.4 V	1.4 V		0.35			0.35		
			I _{OL} = 8 mA	1.65 V	1.65 V		0.45			0.45		
			I _{OL} = 9 mA	2.3 V	2.3 V		0.55			0.55		
			I _{OL} = 12 mA	3 V	3 V		0.7			0.7		
	Input leakage	Control in = V _{CCA} or	buts (xDIR, x OE): V _I GND	0.65 V- 3.6 V	0.65 V- 3.6 V	-0.5	0.5	-1		1	μ	
I	current	Data Input V _I = V _{CCI} o	s (xAx, xBx) or GND	0.65 V- 3.6 V	0.65 V- 3.6 V	-4	4	-8		8	μA	
	Partial power	A or B Poi		0 V	0 V - 3.6 V	-4	4	-8		8	μ/	
off	down current	V _I or V _O =	0 V - 3.6 V	0 V - 3.6 V	0 V	-4	4	-8		8	μ	
oz	Tri-state output current ⁽³⁾	A or B Por V _I = V _{CCI} o or GND, C	or GND, V _O = V _{CCO}	3.6 V	3.6 V	-4	4	-8		8	µ۸	
				0.65 V- 3.6 V	0.65 V- 3.6 V		13			26		
CCA	V _{CCA} supply current	V _I = V _{CCI} or GND	I _O = 0	0 V	3.6 V	-2		-12			μ	
	ourion			3.6 V	0 V		8			16		
				0.65 V- 3.6 V	0.65 V- 3.6 V		13			26		
ССВ	V _{CCB} supply current	V _I = V _{CCI} or GND	I _O = 0	0 V	3.6 V		8			16	μ	
	ourront			3.6 V	0 V	-2		-12				
CCA + CCB	Combined supply current	V _I = V _{CCI} or GND	I _O = 0	0.65 V- 3.6 V	0.65 V- 3.6 V		20			40	μA	
Ci	Control input capacitance	V _I = 3.3 V	or GND	3.3 V	3.3 V		4.5		4.5		pl	
C _{io}	Data I/O capacitance		_A , V _O = 1.65V DC +1 Bm sine wave	3.3 V	3.3 V		6.6		6.6		pl	

over operating free-air temperature range (unless otherwise noted) (1) (2)

(1)

 V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port. (2)

For I/O ports, the parameter I_{OZ} includes the input leakage current. All typical data is taken at 25°C.

(3) (4)



6.6 Switching Characteristics, V_{CCA} = 0.7 V

					B-Port Supply Voltage (V _{CCB})																																
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0.05 V 0.8		0.8 ± 0	0.8 ± 0.04 V		0.9 ± 0.045 V		1.2 ± 0.1 V		1.5 ± 0.1 V		.15 V	2.5 ± 0.2 V		3.3 ± 0.3 V		UNIT																
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX																	
		А	в	–40°C to 85°C	0.5	155	0.5	108	0.5	76	0.5	40	0.5	37	0.5	40	0.5	67	0.5	185																	
	Propagation			–40°C to 125°C	0.5	155	0.5	108	0.5	76	0.5	40	0.5	37	0.5	40	0.5	67	0.5	185																	
t _{pd}	delay B	delay		A	–40°C to 85°C	0.5	156	0.5	128	0.5	106	0.5	55	0.5	21	0.5	15	0.5	11	0.5	10	ns															
				–40°C to 125°C	0.5	156	0.5	128	0.5	106	0.5	55	0.5	21	0.5	15	0.5	11	0.5	10																	
				OE	A	–40°C to 85°C	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156															
t _{dis}	Disable time			–40°C to 125°C	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	0.5	156	ns																
^t dis		ŌĒ	В	–40°C to 85°C	0.5	154	0.5	121	0.5	101	0.5	55	0.5	54	0.5	56	0.5	65	0.5	125																	
		OE B	OE B	VE	UE			–40°C to 125°C	0.5	154	0.5	121	0.5	101	0.5	55	0.5	54	0.5	56	0.5	65	0.5	125													
																			^	–40°C to 85°C	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	
+	Enable time		OE A	–40°C to 125°C	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	0.5	238	ns																
t _{en}												–40°C to 85°C	0.5	286	0.5	194	0.5	146	0.5	94	0.5	76	0.5	70	0.5	69	0.5	146									
			OE B -	–40°C to 125°C	0.5	286	0.5	194	0.5	146	0.5	94	0.5	76	0.5	70	0.5	69	0.5	146																	

See Figure 1 and Table 1 for test circuit and loading. See Figure 2, Figure 3, and Figure 4 for measurement waveforms.

6.7 Switching Characteristics, $V_{CCA} = 0.8 V$

										l	B-Port S	Supply	Voltage	(V _{ссв})																						
PARAMETER		FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± ().1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± (0.3 V	UNIT															
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX																
		^	В	–40°C to 85°C	0.5	128	0.5	88	0.5	63	0.5	29	0.5	24	0.5	23	0.5	24	0.5	34																
	t _{pd} Propagation delay	A	D	–40°C to 125°C	0.5	128	0.5	88	0.5	63	0.5	29	0.5	24	0.5	23	0.5	24	0.5	34																
^L pd		в	^	–40°C to 85°C	0.5	108	0.5	88	0.5	70	0.5	38	0.5	21	0.5	15	0.5	11	0.5	10	ns															
				–40°C to 125°C	0.5	108	0.5	88	0.5	70	0.5	38	0.5	21	0.5	15	0.5	11	0.5	10																
		ŌE A	ŌE A	ŌE A	OE A	ŌE A	ŌE A	ŌE A	ŌE A	OF	OE	OE			OF			^	–40°C to 85°C	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	
+	Disable time										–40°C to 125°C	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	0.5	103	ns								
t _{dis}	Disable time	ŌE B	DE B	ŌE B	ŌE B		–40°C to 85°C	0.5	143	0.5	110	0.5	90	0.5	42	0.5	36	0.5	36	0.5	37	0.5	47	115												
						OE B	OE B	OE B	OE B	E B	JE B	DE B –	–40°C to 125°C	0.5	143	0.5	110	0.5	90	0.5	42	0.5	36	0.5	36	0.5	37	0.5	47							

	- igaio i ana i		1001 011	cuit and loading.	see rig	u. u 2, i	- igaio c	, and	- iguio		Sacaro										
										l	B-Port S	Supply	Voltage	(V _{CCB})							
P.	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± 0).2 V	3.3 ± 0	0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		OE	^	–40°C to 85°C	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	
+	Enable time			–40°C to 125°C	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	0.5	143	ns
Len		OE	В	–40°C to 85°C	0.5	243	0.5	172	0.5	129	0.5	79	0.5	60	0.5	54	0.5	48	0.5	53	115
				–40°C to 125°C	0.5	243	0.5	172	0.5	129	0.5	79	0.5	60	0.5	54	0.5	48	0.5	53	

See Figure 1 and Table 1 for test circuit and loading. See Figure 2, Figure 3, and Figure 4 for measurement waveforms.

6.8 Switching Characteristics, V_{CCA} = 0.9 V

										I	B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± (0.2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		A	в	–40°C to 85°C	0.5	106	0.5	70	0.5	53	0.5	24	0.5	18	0.5	17	0.5	16	0.5	19	
	Propagation		D	–40°C to 125°C	0.5	106	0.5	70	0.5	53	0.5	24	0.5	18	0.5	17	0.5	16	0.5	19	ns
t _{pd}	delay	в	A	–40°C to 85°C	0.5	76	0.5	63	0.5	53	0.5	27	0.5	18	0.5	13	0.5	10	0.5	9	
				–40°C to 125°C	0.5	76	0.5	63	0.5	53	0.5	27	0.5	18	0.5	13	0.5	10	0.5	9	
		OE	A	–40°C to 85°C	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	
t _{dis}	Disable time	UE	A	–40°C to 125°C	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	0.5	81	ns
¹ dis		ŌE	в	–40°C to 85°C	0.5	138	0.5	105	0.5	84	0.5	37	0.5	30	0.5	28	0.5	26	0.5	30	115
				–40°C to 125°C	0.5	138	0.5	105	0.5	84	0.5	37	0.5	30	0.5	28	0.5	26	0.5	30	
		ŌĒ	A	–40°C to 85°C	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	
	Enable time	UE	A	–40°C to 125°C	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	0.5	95	
t _{en}		ŌE	в	–40°C to 85°C	0.5	222	0.5	148	0.5	116	0.5	71	0.5	52	0.5	46	0.5	39	0.5	39	ns
				–40°C to 125°C	0.5	222	0.5	148	0.5	116	0.5	71	0.5	52	0.5	46	0.5	39	0.5	39	



6.9 Switching Characteristics, V_{CCA} = 1.2 V

											B-Port S	Supply	Voltage	(V _{CCB})							
P/	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± ().1 V	1.5 ± ().1 V	1.8 ± 0	.15 V	2.5 ± (0.2 V	3.3 ± (0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	в	–40°C to 85°C	0.5	55	0.5	37	0.5	27	0.5	15	0.5	11	0.5	10	0.5	8	0.5	9	
	Propagation	A		–40°C to 125°C	0.5	55	0.5	37	0.5	27	0.5	15	0.5	11	0.5	10	0.5	8	0.5	9	
t _{pd}	delay	в		–40°C to 85°C	0.5	41	0.5	29	0.5	24	0.5	15	0.5	10	0.5	9	0.5	7	0.5	6	ns
		D	A	–40°C to 125°C	0.5	41	0.5	29	0.5	24	0.5	15	0.5	10	0.5	9	0.5	7	0.5	6	
		ŌE	A	–40°C to 85°C	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	
+	Disable time			–40°C to 125°C	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	0.5	30	ns
t _{dis}		ŌĒ	В	–40°C to 85°C	0.5	132	0.5	99	0.5	79	0.5	31	0.5	24	0.5	21	0.5	18	0.5	18	115
				–40°C to 125°C	0.5	132	0.5	99	0.5	79	0.5	31	0.5	24	0.5	21	0.5	18	0.5	18	
		ŌĒ	A	–40°C to 85°C	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	
+	Enable time			–40°C to 125°C	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	0.5	45	nc
t _{en}		ŌE	в	–40°C to 85°C	0.5	164	0.5	108	0.5	79	0.5	58	0.5	41	0.5	35	0.5	27	0.5	24	ns
				–40°C to 125°C	0.5	164	0.5	108	0.5	79	0.5	58	0.5	41	0.5	35	0.5	27	0.5	24	

See Figure 1 and Table 1 for test circuit and loading. See Figure 2, Figure 3, and Figure 4 for measurement waveforms.

6.10 Switching Characteristics, V_{CCA} = 1.5 V

											B-Port S	Supply	Voltage	(V _{CCB})							
	PARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± (0.2 V	3.3 ± (0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	В	–40°C to 85°C	0.5	21	0.5	21	0.5	18	0.5	11	0.5	9	0.5	8	0.5	7	0.5	6	
	Propagation	A	D	–40°C to 125°C	0.5	21	0.5	21	0.5	18	0.5	11	0.5	9	0.5	8	0.5	7	0.5	6	
t _{pd}	delay	в	^	–40°C to 85°C	0.5	37	0.5	24	0.5	18	0.5	11	0.5	9	0.5	8	0.5	5	0.5	5	ns
		D		–40°C to 125°C	0.5	37	0.5	24	0.5	18	0.5	11	0.5	9	0.5	8	0.5	5	0.5	5	
		ŌE	^	–40°C to 85°C	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	
t	Disable time	UE	A	–40°C to 125°C	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	0.5	21	ns
t _{dis}		OE	В	–40°C to 85°C	0.5	131	0.5	97	0.5	77	0.5	29	0.5	21	0.5	19	0.5	15	0.5	15	115
				–40°C to 125°C	0.5	131	0.5	97	0.5	77	0.5	29	0.5	21	0.5	19	0.5	15	0.5	15	

										I	B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		OE	Δ	–40°C to 85°C	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	
+	Enable time			–40°C to 125°C	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	0.5	26	ns
Len		OE	в	–40°C to 85°C	0.5	109	0.5	84	0.5	68	0.5	47	0.5	35	0.5	29	0.5	22	0.5	20	
			D	–40°C to 125°C	0.5	109	0.5	84	0.5	68	0.5	47	0.5	35	0.5	29	0.5	22	0.5	20	

See Figure 1 and Table 1 for test circuit and loading. See Figure 2, Figure 3, and Figure 4 for measurement waveforms.

6.11 Switching Characteristics, V_{CCA} = 1.8 V

										I	B-Port S	Supply	Voltage	(V _{ссв})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± ().1 V	1.8 ± 0	.15 V	2.5 ± (0.2 V	3.3 ± (0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	В	–40°C to 85°C	0.5	15	0.5	15	0.5	13	0.5	9	0.5	8	0.5	7	0.5	6	0.5	6	
+	Propagation	A		–40°C to 125°C	0.5	15	0.5	15	0.5	13	0.5	9	0.5	8	0.5	7	0.5	6	0.5	6	ns
t _{pd}	delay	в	A	–40°C to 85°C	0.5	40	0.5	23	0.5	17	0.5	10	0.5	8	0.5	7	0.5	5	0.5	4	115
		D		–40°C to 125°C	0.5	40	0.5	23	0.5	17	0.5	10	0.5	8	0.5	7	0.5	5	0.5	4	
		OE	A	–40°C to 85°C	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	
+	Disable time			–40°C to 125°C	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	0.5	18	ns
t _{dis}		OE	В	–40°C to 85°C	0.5	130	0.5	96	0.5	76	0.5	28	0.5	21	0.5	18	0.5	15	0.5	14	
				–40°C to 125°C	0.5	130	0.5	96	0.5	76	0.5	28	0.5	21	0.5	18	0.5	15	0.5	14	
		ŌE	A	–40°C to 85°C	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	
	Enable time	UE	A	–40°C to 125°C	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	0.5	20	
t _{en}		ŌE	в	–40°C to 85°C	0.5	102	0.5	75	0.5	62	0.5	41	0.5	32	0.5	27	0.5	20	0.5	18	ns
				–40°C to 125°C	0.5	102	0.5	75	0.5	62	0.5	41	0.5	32	0.5	27	0.5	20	0.5	18	



6.12 Switching Characteristics, V_{CCA} = 2.5 V

										I	B-Port S	Supply	Voltage	(V _{CCB})							
P.	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		А	в	–40°C to 85°C	0.5	11	0.5	11	0.5	10	0.5	7	0.5	5	0.5	5	0.5	5	0.5	5	
	Propagation	^		–40°C to 125°C	0.5	11	0.5	11	0.5	11	0.5	7	0.5	5	0.5	5	0.5	5	0.5	5	ns
t _{pd}	delay	в	A	–40°C to 85°C	0.5	67	0.5	24	0.5	16	0.5	8	0.5	7	0.5	6	0.5	5	0.5	4	115
		В		–40°C to 125°C	0.5	67	0.5	24	0.5	16	0.5	8	0.5	7	0.5	6	0.5	5	0.5	4	
		OE	A	–40°C to 85°C	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	
t.	Disable time			–40°C to 125°C	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	ns
t _{dis}		OE	В	–40°C to 85°C	0.5	128	0.5	95	0.5	76	0.5	27	0.5	20	0.5	17	0.5	13	0.5	13	115
				–40°C to 125°C	0.5	128	0.5	95	0.5	76	0.5	27	0.5	20	0.5	17	0.5	13	0.5	13	
		OE	A	–40°C to 85°C	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	
•	Enable time			–40°C to 125°C	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	0.5	13	ne
t _{en}		OE	в	–40°C to 85°C	0.5	120	0.5	70	0.5	56	0.5	36	0.5	26	0.5	22	0.5	18	0.5	16	ns
				–40°C to 125°C	0.5	120	0.5	70	0.5	56	0.5	36	0.5	26	0.5	22	0.5	18	0.5	16	

See Figure 1 and Table 1 for test circuit and loading. See Figure 2, Figure 3, and Figure 4 for measurement waveforms.

6.13 Switching Characteristics, V_{CCA} = 3.3 V

										l	B-Port S	Supply	Voltage	(V _{CCB})							
	PARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± (0.3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		^	В	–40°C to 85°C	0.5	10	0.5	10	0.5	9	0.5	6	0.5	5	0.5	4	0.5	4	0.5	4	
	Propagation	A	D	–40°C to 125°C	0.5	10	0.5	10	0.5	9	0.5	6	0.5	5	0.5	4	0.5	4	0.5	4	
t _{pd}	delay	в	^	–40°C to 85°C	0.5	185	0.5	34	0.5	19	0.5	9	0.5	6	0.5	6	0.5	5	0.5	4	ns
				–40°C to 125°C	0.5	185	0.5	34	0.5	19	0.5	9	0.5	6	0.5	6	0.5	5	0.5	4	
		ŌĒ	^	–40°C to 85°C	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	
t	Disable time	UE	A	–40°C to 125°C	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	0.5	12	
t _{dis}		ŌE	В	–40°C to 85°C	0.5	141	0.5	95	0.5	75	0.5	27	0.5	19	0.5	17	0.5	13	0.5	12	ns
				–40°C to 125°C	0.5	141	0.5	95	0.5	75	0.5	27	0.5	19	0.5	17	0.5	13	0.5	12	



											B-Port S	Supply	Voltage	(V _{CCB})							
P	ARAMETER	FROM	то	Test Conditions	0.7 ± 0	.05 V	0.8 ± 0	.04 V	0.9 ± 0.	045 V	1.2 ± (0.1 V	1.5 ± (0.1 V	1.8 ± 0	.15 V	2.5 ± ().2 V	3.3 ± ().3 V	UNIT
					MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
		OE	Δ	–40°C to 85°C	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	
•	Enable time			–40°C to 125°C	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	0.5	11	ns
Len		ŌE	в	–40°C to 85°C	0.5	189	0.5	82	0.5	59	0.5	35	0.5	24	0.5	20	0.5	16	0.5	14	115
				–40°C to 125°C	0.5	189	0.5	82	0.5	59	0.5	35	0.5	24	0.5	20	0.5	16	0.5	14	



6.14 Operating Characteristics: T_A = 25°C

	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN TYP	MAX	UNIT
			0.7 V	0.7 V	2.2		
			0.8 V	0.8 V	2.1		
			0.9 V	0.9 V	2.1		
	Power Dissipation Capacitance per transceiver (A to B: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	2.1		pF
	enabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	2.0		рг
			1.8 V	1.8 V	2.0		
			2.5 V	2.5 V	2.1		
			3.3 V	3.3 V	2.3		
			0.7 V	0.7 V	1.5		
			0.8 V	0.8 V	1.5		
			0.9 V	0.9 V	1.5		
	Power Dissipation Capacitance per transceiver (A to B: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	1.4		pF
	disabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	1.4		рг
			1.8 V	1.8 V	1.4		
			2.5 V	2.5 V	1.4		
C			3.3 V	3.3 V	1.6		
C _{pdA}			0.7 V	0.7 V	12.1		
			0.8 V	0.8 V	12.1		
			0.9 V	0.9 V	12.1		
	Power Dissipation Capacitance per transceiver (B to A: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	12.4		pF
	enabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	13.0		рг
			1.8 V	1.8 V	14.2		
			2.5 V	2.5 V	17.4		
			3.3 V	3.3 V	20.1		
			0.7 V	0.7 V	1.1		
			0.8 V	0.8 V	1.1		
			0.9 V	0.9 V	1.1		
	Power Dissipation Capacitance per transceiver (B to A: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	1.1		pF
	disabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	1.1		Ы
			1.8 V	1.8 V	1.1		
			2.5 V	2.5 V	1.1		
			3.3 V	3.3 V	1.1		

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	PARAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN TYP	MAX	UNIT
			0.7 V	0.7 V	12.1		
			0.8 V	0.8 V	12.1		
			0.9 V	0.9 V	12.1		
	Power Dissipation Capacitance per transceiver (A to B: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	12.4		" Г
	enabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	12.9		pF
			1.8 V	1.8 V	14.1		
			2.5 V	2.5 V	17.2		
			3.3 V	3.3 V	20.1		
			0.7 V	0.7 V	1.1		
			0.8 V	0.8 V	1.1		
			0.9 V	0.9 V	1.1		
	Power Dissipation Capacitance	CL = 0, RL = Open f = 1	1.2 V	1.2 V	1.1		
	per transceiver (A to B: outputs disabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	1.1		pF
	,		1.8 V	1.8 V	1.1		
			2.5 V	2.5 V	1.1		
			3.3 V	3.3 V	1.1		
C _{pdB}			0.7 V	0.7 V	1.2		
			0.8 V	0.8 V	1.8		
			0.9 V	0.9 V	1.8		
	Power Dissipation Capacitance per transceiver (B to A: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	1.7		рF
	enabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	1.7		рг
			1.8 V	1.8 V	1.7		
			2.5 V	2.5 V	2		
			3.3 V	3.3 V	2.5		
			0.7 V	0.7 V	1.1		
			0.8 V	0.8 V	1.8		
			0.9 V	0.9 V	1.8		
	Power Dissipation Capacitance per transceiver (B to A: outputs	CL = 0, RL = Open f = 1	1.2 V	1.2 V	1.7		"Г
	disabled)	MHz, tr = tf = 1 ns	1.5 V	1.5 V	1.7		pF
	, ,		1.8 V	1.8 V	1.7		
			2.5 V	2.5 V	2		
			3.3 V	3.3 V	2.1		

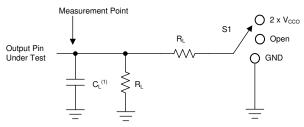


7 Parameter Measurement Information

7.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1 MHz
- Z_O = 50 Ω
- dv/dt ≤ 1 ns/V

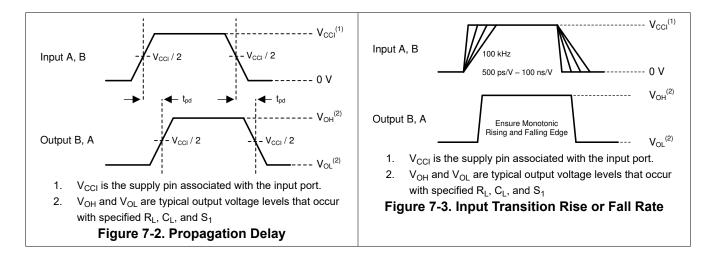


A. C_L includes probe and jig capacitance.

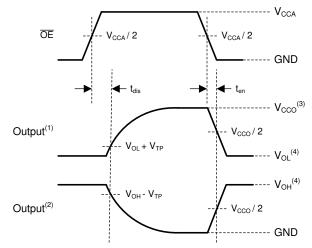
Figure 7-1. Load Circuit

Table 7-1. Load Circuit Conditions

				Conditions		
	Parameter	V _{cco}	RL	CL	S ₁	V _{TP}
Δt/Δv	Input transition rise or fall rate	0.65 V – 3.6 V	1 MΩ	15 pF	Open	N/A
		1.1 V – 3.6 V	2 kΩ	15 pF	Open	N/A
t _{pd}	Propagation (delay) time	0.65 V – 0.95 V	20 kΩ	15 pF	Open	N/A
		3 V – 3.6 V	2 kΩ	15 pF	2 × V _{CCO}	0.3 V
		1.65 V – 2.7 V	2 kΩ	15 pF	2 × V _{CCO}	0.15 V
t _{en} , t _{dis}	Enable time, disable time	1.1 V – 1.6 V	2 kΩ	15 pF	2 × V _{CCO}	0.1 V
		0.65 V – 0.95 V	20 kΩ	15 pF	2 × V _{CCO}	0.1 V
		3 V – 3.6 V	2 kΩ	15 pF	GND	0.3 V
		1.65 V – 2.7 V	2 kΩ	15 pF	GND	0.15 V
en, t _{dis}	Enable time, disable time	1.1 V – 1.6 V	2 kΩ	15 pF	GND	0.1 V
		0.65 V – 0.95 V	20 kΩ	15 pF	GND	0.1 V







- A. Output waveform on the condition that input is driven to a valid Logic Low.
- B. Output waveform on the condition that input is driven to a valid Logic High.
- C. V_{CCO} is the supply pin associated with the output port.
- D. V_{OH} and V_{OL} are typical output voltage levels with specified R_L, C_L, and S_1.

Figure 7-4. Enable Time And Disable Time

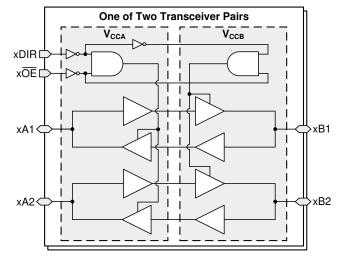


8 Detailed Description

8.1 Overview

The SN74AXC4T245 is a 4-bit, dual-supply noninverting bidirectional voltage level translation device. Ax pins and control pins (1DIR, 2DIR,1 \overline{OE} , and 2 \overline{OE}) are referenced to V_{CCA} logic levels, and Bx pins are referenced to V_{CCB} logic levels. The A port is able to accept I/O voltages ranging from 0.65 V to 3.6 V, while the B port can accept I/O voltages from 0.65 V to 3.6 V. A high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A when \overline{OE} is set to low. When \overline{OE} is set to high, both Ax and Bx pins are in the high-impedance state. See *Device Functional Modes* for a summary of the operation of the control logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law ($R = V \div I$).

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t/\Delta v$ in *Recommended Operating Conditions* to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.

8.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

8.3.3 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

8.3.4 V_{CC} Isolation

The inputs and outputs for this device enter a high-impedance state when either supply is <100mV.



8.3.5 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

8.3.6 Glitch-free Power Supply Sequencing

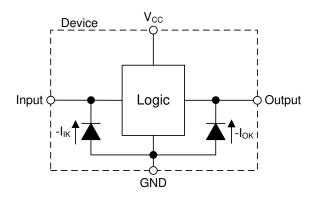
Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral. For more information regarding the power up glitch performance of the AXC family of level translators, see the *Glitch Free Power Sequencing With AXC Level Translators* application report

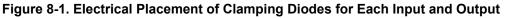
8.3.7 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 8-1.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.





8.3.8 Fully Configurable Dual-Rail Design

Both the V_{CCA} and V_{CCB} pins can be supplied at any voltage from 0.65 V to 3.6 V, making the device suitable for translating between any of the voltage nodes (0.7 V, 0.8 V, 0.9 V, 1.2 V, 1.8 V, 2.5 V and 3.3 V).

8.3.9 Supports High-Speed Translation

The SN74AXC4T245 device can support high data-rate applications. The translated signal data rate can be up to 380 Mbps when the signal is translated from 1.8 V to 3.3 V.

8.4 Device Functional Modes

Table 8-1. Function Table (Each 2-Bit Section)									
CONTROL INPUTS ⁽¹⁾ PORT STATUS OPERATION									
ŌĒ	DIR	OPERATION							
L	L	Output (Enabled)	Input (Hi-Z)	B data to A bus					
L	Н	Input (Hi-Z)	Output (Enabled)	A data to B bus					
Н	Х	Input (Hi-Z)	Input (Hi-Z)	Isolation					

(1) Input circuits of the data I/Os are always active.



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74AXC4T245 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74AXC4T245 device is ideal for use in applications where a push-pull driver is connected to the data I/Os. The max data rate can be up to 380 Mbps when device translates a signal from 1.8 V to 3.3 V.

One example application is shown in Figure 9-1, where the SN74AXC4T245 device is used to translate a low voltage UART signal from an SoC to a higher voltage signal which properly drive the inputs of the bluetooth module, and vice versa.



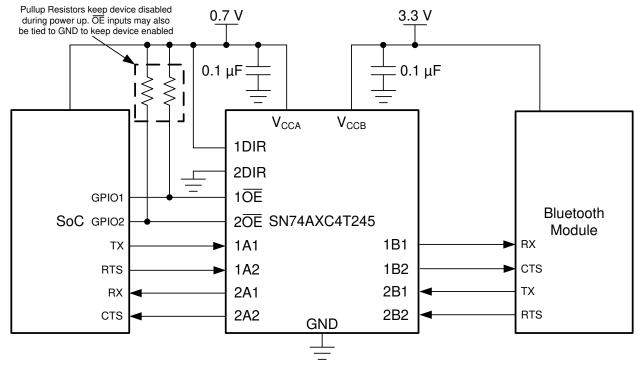


Figure 9-1. UART Interface Application

9.2.1 Design Requirements

For this design example, use the parameters listed in Table 9-1.

Table 9-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES						
Input voltage range	0.65 V to 3.6 V						
Output voltage range	0.65 V to 3.6 V						

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9.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
 - Use the supply voltage of the device that is driving the SN74AXC4T245 device to determine the input voltage range. For a valid logic-high, the value must exceed the high-level input voltage (V_{IH}) of the input port. For a valid logic low the value must be less than the low-level input voltage (V_{IL}) of the input port.
- Output voltage range
 - Use the supply voltage of the device that the SN74AXC4T245 device is driving to determine the output voltage range.

9.2.3 Application Curve

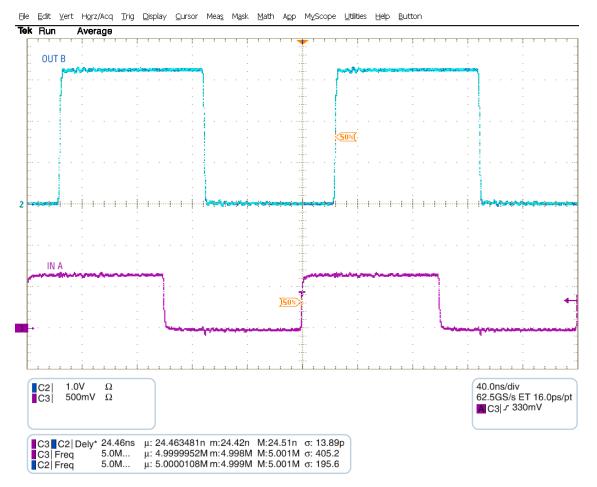


Figure 9-2. Up Translation at 2.5 MHz (0.7 V to 3.3 V)



10 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices. For more information regarding the power up glitch performance of the AXC family of level translators, see the *Glitch Free Power Sequencing With AXC Level Translators* application report

11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible.
- Use short trace lengths to avoid excessive loading.

11.2 Layout Example

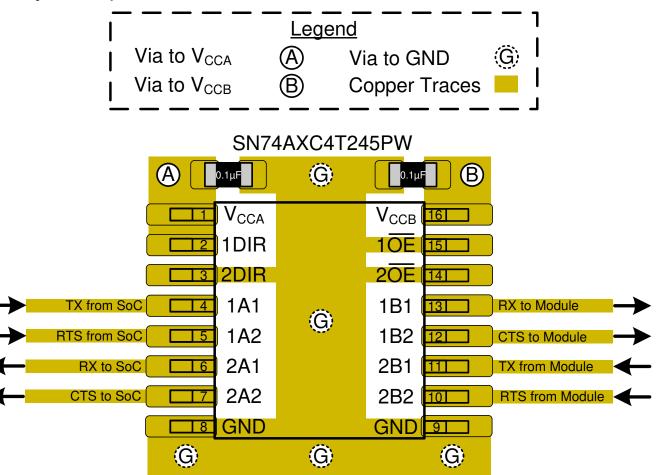


Figure 11-1. Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

Texas Instruments, Implications of Slow or Floating CMOS Inputs application report

Texas Instruments, Power Sequencing for AXC Family of Devices application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



11-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AXC4T245BQBR	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	4T245	Samples
SN74AXC4T245PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	SN4T245	Samples
SN74AXC4T245RSVR	ACTIVE	UQFN	RSV	16	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1TIR	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

11-Dec-2020

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AXC4T245 :

• Automotive: SN74AXC4T245-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



Texas

*All dimensions are nominal

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AXC4T245BQBR	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74AXC4T245PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AXC4T245PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AXC4T245RSVR	UQFN	RSV	16	3000	178.0	13.5	2.1	2.9	0.75	4.0	12.0	Q1



www.ti.com

PACKAGE MATERIALS INFORMATION

16-Jun-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AXC4T245BQBR	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74AXC4T245PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74AXC4T245PWR	TSSOP	PW	16	2000	364.0	364.0	27.0
SN74AXC4T245RSVR	UQFN	RSV	16	3000	189.0	185.0	36.0

PW0016A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



PW0016A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PW0016A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

BQB 16

GENERIC PACKAGE VIEW

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

2.5 x 3.5, 0.5 mm pitch

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





BQB0016A

PACKAGE OUTLINE

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



BQB0016A

EXAMPLE BOARD LAYOUT

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

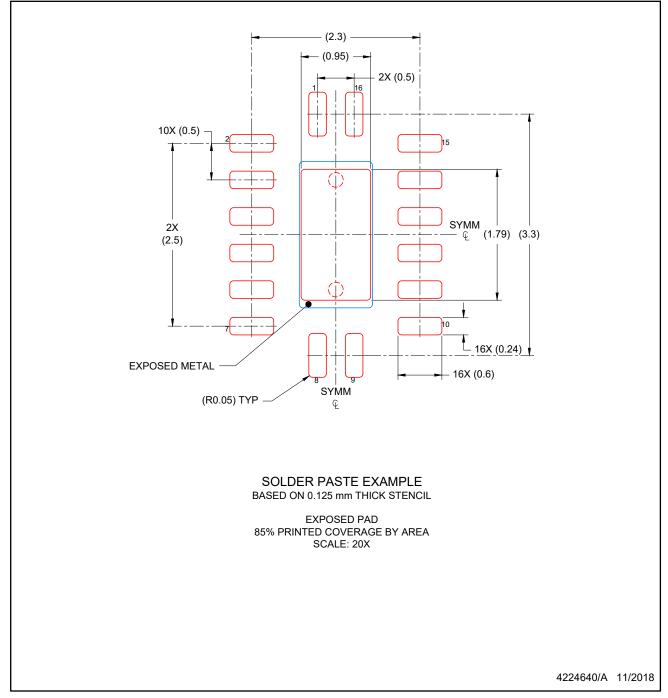


BQB0016A

EXAMPLE STENCIL DESIGN

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



RSV0016A



PACKAGE OUTLINE

UQFN - 0.55 mm max height

ULTRA THIN QUAD FLATPACK - NO LEAD



NOTES:

All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
This drawing is subject to change without notice.

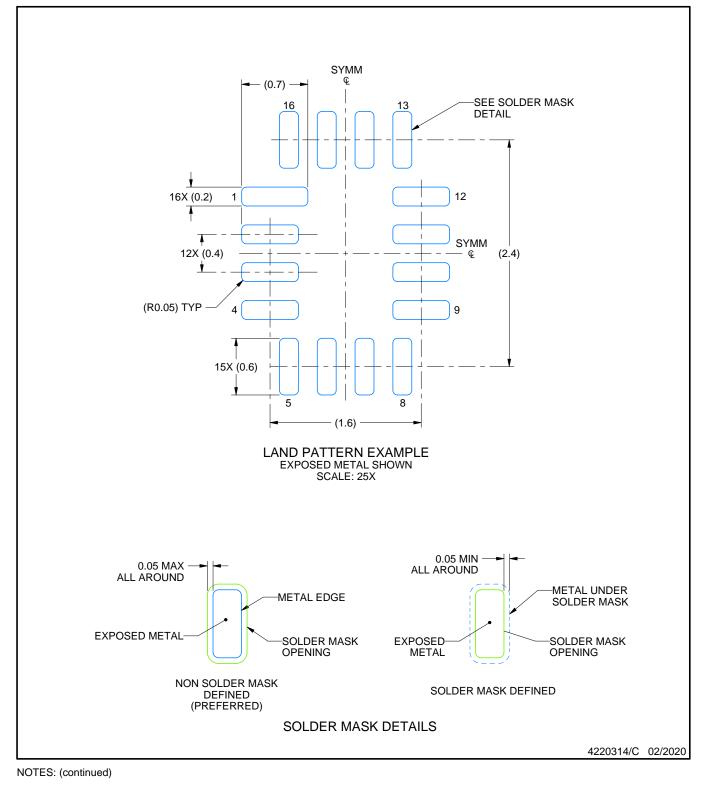


RSV0016A

EXAMPLE BOARD LAYOUT

UQFN - 0.55 mm max height

ULTRA THIN QUAD FLATPACK - NO LEAD



3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

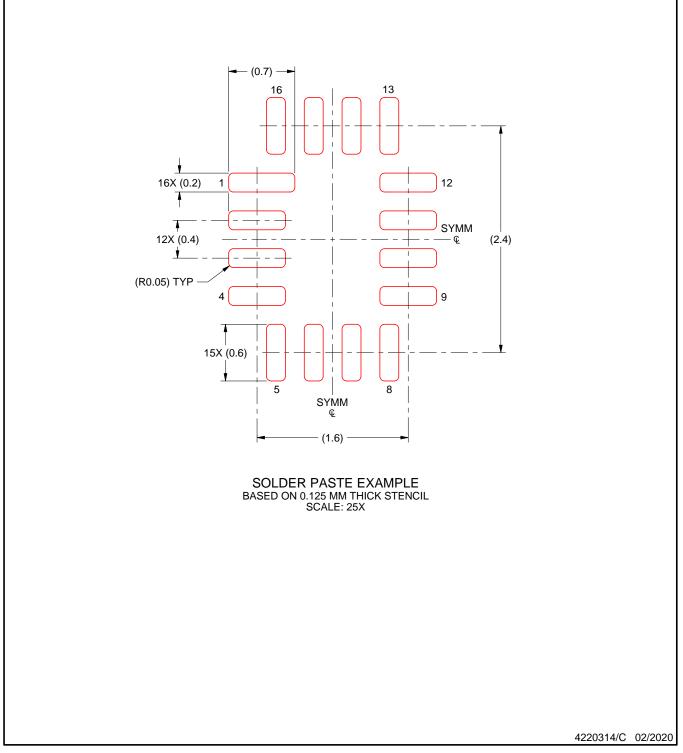


RSV0016A

EXAMPLE STENCIL DESIGN

UQFN - 0.55 mm max height

ULTRA THIN QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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